Day : Monday
Date: 5/23/2005

PALM INTRANET

Time: 10:18:09

Inventor Name Search Result

Your Search was:

Last Name = LI
First Name = LI

Application#	Patent#	Status	Date Filed	Title	Inventor Name 42
60660475	Not Issued	020	03/10/2005	BIPHENYL COMPOUNDS USEFUL AS MUSCARINIC RECEPTOR ANTAGONISTS	LI, LI
60646610	Not Issued	020	01/26/2005	USE OF SFRPS AS MARKERS OF BMP ACTIVITY	LI, LI
60646515	Not Issued	020	01/25/2005	THIN FILM OPTICAL DEVICES AND A METHOD OF MANUFACTURING SUCH DEVICES	LI, LI
60361833	Not Issued	159	03/05/2002	NADP-DEPENDENT MALIC ENZYME-LIKE PROTEINS, DERIVED PEPTIDES, AND NUCLEIC ACIDS ENCODING SAME	LI, LI
60360858	Not Issued	159	03/01/2002	NOVEL ALDOSE REDUCTASE-RELATED PROTEIN-LIKE PROTEINS AND NUCLEIC ACIDS ENCODING SAME	LI, LI
60360830	Not Issued	159	03/01/2002	NOVEL AROMATIC-L-AMINO ACID DECARBOXYLASE-LIKE PROTEINS AND NUCLEIC ACIDS ENCODING SAME	LI, LI
60359944	Not Issued	159	02/27/2002	L-SERINE DEHYDRATASE-LIKE PROTEINS, DERIVED PEPTIDES, AND NUCLEIC ACIDS ENCODING SAME	LI, LI
60348283	Not Issued	159	11/09/2001	NOVEL HUMAN PROTEINS AND NUCLEIC ACIDS ENCODING SAME	LI, LI
60345221	Not Issued	159	01/04/2002	NOVEL MAP KINASE-ACTIVATING DEATH DOMAIN PROTEIN-LIKE PROTEINS AND NUCLEIC ACIDS ENCODING SAME	LI, LI

60343629	Not Issued	159	10/24/2001	NOVEL HUMAN PROTEINS AND NUCLEIC ACIDS ENCODING SAME	LI, LI
60341354	Not Issued	159	12/14/2001	NOVEL UROPLAKIN 1B-LIKE PROTEINS AND NUCLEIC ACIDS ENCODING SAME	LI, LI
60340225	Not Issued	159	12/14/2001	NOVEL KETOHEXOKINASE-LIKE PROTEINS AND NUCLEIC ACIDS ENCODING SAME	LI, LI
60338285	Not Issued	159	12/07/2001	NOVEL HUMAN PROTEINS AND NUCLEIC ACIDS ENCODING SAME	LI, LI
11095624	Not Issued	018	03/31/2005	CNGH0011 POLYNUCLEOTIDES, POLYPEPTIDES, ANTIBODIES, AND COMPOSITIONS, AND METHODS OF PRODUCTION AND USE	LI, LI
11087218	Not Issued	020	03/23/2005	METHODS OF FORMING TRENCH ISOLATION IN THE FABRICATION OF INTEGRATED CIRCUITRY AND METHODS OF FABRICATING INTEGRATED CIRCUITRY	LI, LI
11084616	Not Issued	020	03/18/2005	SYSTEM AND METHOD FOR UTILIZING THE CONTENT OF AUDIO/VIDEO FILES TO SELECT ADVERTISING CONTENT FOR DISPLAY	LI, LI
11079924	Not Issued	019	03/14/2005	CAPACITOR STRUCTURE	LI, LI
11077433	Not Issued	020	03/10/2005	BIPHENYL COMPOUNDS USEFUL AS MUSCARINIC RECEPTOR ANTAGONISTS	LI, LI
11076796	Not Issued	020	03/10/2005	BIPHENYL COMPOUNDS USEFUL AS MUSCARINIC RECEPTOR ANTAGONISTS	LI, LI
11076658	Not Issued	020	03/10/2005	DIPHENYLMETHYL COMPOUNDS USEFUL AS MUSCARINIC RECEPTOR ANTAGONISTS	LI, LI
11074099	Not Issued	020	03/07/2005	SYSTEM AND METHOD FOR PROVIDING INSTANT MESSAGING CAPABILITY IN CONJUNCTION WITH AN ONLINE REFERENCE	LI, LI

11072452	Not Issued	020	03/07/2005	FORMATION OF MICRO LENS BY USING FLOWABLE OXIDE DEPOSITION	LI, LI
11061821	Not Issued	019	01/01/0001	METHODS AND COMPOSITIONS FOR TREATING IL-3 RELATED PATHOLOGIES	LI, LI
11051724	Not Issued	019	02/02/2005	THERAPEUTIC POLYPEPTIDES, NUCLEIC ACIDS ENCODING SAME, AND METHODS OF USE	LI, LI
11044302	Not Issued	030	01/28/2005	ANY GEAR START HORIZONTAL ENGINE FOR MOTORCYCLE	LI, LI
11009282	Not Issued	020	12/10/2004	METHODS OF ENHANCING SELECTIVITY OF ETCHING SILICON DIOXIDE RELATIVE TO ONE OR MORE ORGANIC SUBSTANCES; AND PLASMA REACTION CHAMBERS	LI, LI
10999586	Not Issued	020	11/30/2004	SYSTEMS AND METHODS FOR DETERMINING RELATIVE PLACEMENT OF CONTENT ITEMS ON A RENDERED PAGE	LI, LI
10975720	Not Issued	030	10/28/2004	EMBEDDED MULTILAYER PRINTED CIRCUIT	LI, LI
10971479	Not Issued	020	10/21/2004	NOVEL HUMAN PROTEINS AND POLYNUCLEOTIDES ENCODING THEM	LI, LI
10024212	Not Issued	161	12/18/2001	NOVEL PROTEINS AND NUCLEIC ACIDS ENCODING SAME	LI, LI
09448556	6399504	150	11/23/1999	METHODS AND ETCHANTS FOR ETCHING OXIDES OF SILICON WITH LOW SELECTIVITY	LI, LI
09431812	6322954	150	11/02/1999	WET INORGANIC AMMONIA ETCH OF ORGANICALLY MASKED SILICON-CONTAINING MATERIAL	LI, LI
09430139	6271968	150	10/29/1999	CUT-OFF FILTERS	LI, LI
09383045	6306774	150	08/25/1999	METHOD OF FORMING A WORDLINE	LI, LI
09323749	6211054	150	06/01/1999	METHOD OF FORMING A	LI, LI

				CONDUCTIVE LINE AND METHOD OF FORMING A LOCAL INTERCONNECT	
09323464	6451127	150	06/01/1999	CONDUCTIVE PASTE AND SEMICONDUCTOR COMPONENT HAVING CONDUCTIVE BUMPS MADE FROM THE CONDUCTIVE PASTE	LI, LI
09305299	6241837	150	05/05/1999	METHOD OF PRODUCING CERAMIC ARTICLE WITH RELIEF DECORATION	LI HO, LIN
09293212	6194315	150	04/16/1999	ELECTROCHEMICAL COBALT SILICIDE LINER FOR METAL CONTACT FILLS AND DAMASCENE PROCESSES	LI, LI
09283666	Not Issued	163	04/01/1999	PLATINUM POST-ETCH CLEAN DURING THE FORMATION OF A SEMICONDUCTOR DEVICE	LI, LI
09283606	6459116	150	04/01/1999	CAPACITOR STRUCTURE	LI, LI
08556878	5825139	150	11/02/1995	LAMP DRIVEN VOLTAGE TRANSFORMATION AND BALLASTING SYSTEM	LI LIN, LILY

Inventor Search Completed: No Records to Display.

Search Another: Inventor **Last Name** Li **First Name** Li Search

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Time: 10:19:59

Inventor Name Search Result

Your Search was:

Last Name = LI
First Name = WEIMIN

Application#	Patent#	Status	Date Filed	Title	Inventor Name 46
10991693	Not Issued	030	11/18/2004	CVD OF PTRH WITH GOOD ADHESION AND MORPHOLOGY	LI, WEIMIN
10931355	Not Issued	071	08/31/2004	PASSIVATION PROCESSES FOR USE WITH METALLIZATION TECHNIQUES	LI, WEIMIN
10916918	Not Issued	030	08/12/2004	GAS DELIVERY SYSTEM FOR DEPOSITION PROCESSES, AND METHODS OF USING SAME	LI, WEIMIN
10913555	Not Issued	041	08/06/2004	CHEMICAL TREATMENT OF SEMICONDUCTOR SUBSTRATES	LI, WEIMIN
10866290	Not Issued	030	06/11/2004	METHOD OF IMPROVING HDP FILL PROCESS	LI, WEIMIN
10853063	Not Issued	030	05/25/2004	METHOD OF ELIMINATING RESIDUAL CARBON FROM FLOWABLE OXIDE FILL	LI, WEIMIN
10806923	Not Issued	030	03/22/2004	METHODS OF DEPOSITING SILICON DIOXIDE COMPRISING LAYERS IN THE FABRICATION OF INTEGRATED CIRCUITRY, METHODS OF FORMING TRENCH ISOLATION, AND METHODS OF FORMING ARRAYS OF MEMORY CELLS	LI, WEIMIN
10789736	Not Issued	030	02/27/2004	TRANSPARENT AMORPHOUS CARBON STRUCTURE IN SEMICONDUCTOR DEVICES	LI, WEIMIN
10776553	Not Issued	041	02/10/2004	COMPOSITIONS OF MATTER AND BARRIER LAYER COMPOSITIONS	LI, WEIMIN
10757638	Not	094	01/13/2004	TECHNIQUE FOR HIGH	LI, WEIMIN

	Issued			EFFICIENCY METALORGANIC CHEMICAL VAPOR DEPOSITION	
10756222	Not Issued	041	01/13/2004	TECHNIQUE FOR HIGH EFFICIENCY METALORGANIC CHEMICAL VAPOR DEPOSITION	LI, WEIMIN
10669671	Not Issued	071	09/23/2003	METHODS OF FILLING GAPS AND METHODS OF DEPOSITING MATERIALS USING HIGH DENSITY PLASMA CHEMICAL VAPOR DEPOSITION	LI, WEIMIN
10669667	Not Issued	030	09/23/2003	ATOMIC LAYER DEPOSITION METHODS OF FORMING SILICON DIOXIDE COMPRISING LAYERS	LI, WEIMIN
10661379	Not Issued	041	09/12/2003	TRANSPARENT AMORPHOUS CARBON STRUCTURE IN SEMICONDUCTOR DEVICES	LI, WEIMIN
10661100	Not Issued	071	09/12/2003	MASKING STRUCTURE HAVING MULTIPLE LAYERS INCLUDING AN AMORPHOUS CARBON LAYER	LI, WEIMIN
10642641	6833605	150	08/19/2003	METHOD OF MAKING A MEMORY CELL CAPACITOR WITH TA2O5 DIELECTRIC	LI, WEIMIN
10618220	Not Issued	094	07/11/2003	METHODS FOR FILLING HIGH ASPECT RATIO TRENCHES IN SEMICONDUCTOR LAYERS	LI, WEIMIN
10460624	6866900	150	06/11/2003	DEPOSITION AND CHAMBER TREATMENT METHODS	LI, WEIMIN
10435791	Not Issued	071	05/12/2003	USE OF SPIN-ON, PHOTOPATTERNABLE, INTERLAYER DIELECTRIC MATERIALS AND INTERMEDIATE SEMICONDUCTOR DEVICE STRUCTURE UTILIZING THE SAME	LI, WEIMIN
10420246	Not Issued	092	04/21/2003	METHOD OF DEPOSITING A SILICON DIOXIDE COMPRISING LAYER DOPED WITH AT LEAST ONE OF P, B AND GE	LI, WEIMIN
10419497	Not	030	04/21/2003	3~6-DOF DECOUPLING	LI, WEIMIN

	Issued			STRUCTURE PARALLEL MICROMANIPULATOR	
10357812	Not Issued	061	02/04/2003	METHOD OF ELIMINATING RESIDUAL CARBON FROM FLOWABLE OXIDE FILL	LI, WEIMIN
10338995	6889141	150	01/10/2003	METHOD AND SYSTEM TO FLEXIBLY CALCULATE HYDRAULICS AND HYDROLOGY OF WATERSHEDS AUTOMATICALLY	LI, WEIMIN
10319694	6756293	150	12/16/2002	COMBINED GATE CAP OR DIGIT LINE AND SPACER DEPOSITION USING HDP	LI, WEIMIN
10284681	Not Issued	094	10/31/2002	GAS DELIVERY SYSTEM FOR DEPOSITION PROCESSES, AND METHODS OF USING SAME	LI, WEIMIN
10234729	6676756	150	08/30/2002	TECHNIQUE FOR HIGH EFFICIENCY METALORGANIC CHEMICAL VAPOR DEPOSITION	LI, WEIMIN
10150843	6777308	150	05/17/2002	METHOD OF IMPROVING HDP FILL PROCESS	LI, WEIMIN
10137384	Not Issued	092	05/03/2002	METHOD OF FABRICATING A SEMICONDUCTOR MULTILEVEL INTERCONNECT STRUCTURE	LI, WEIMIN
10102110	Not Issued	093	03/19/2002	LOW K INTERLEVEL DIELECTRIC LAYER FABRICATION METHODS	LI, WEIMIN
10033656	6835995	150	12/27/2001	LOW DIELECTRIC CONSTANT MATERIAL FOR INTEGRATED CIRCUIT FABRICATION	LI, WEIMIN
10005439	6573571	150	12/03/2001	SEMICONDUCTOR STRUCTURE INCLUDING METAL NITRIDE AND METAL SILICIDE LAYERS OVER ACTIVE AREA AND GATE STACK	LI, WEIMIN
09629998	6281072	150	08/01/2000	MULTIPLE STEP METHODS FOR FORMING CONFORMAL LAYERS	LI, WEIMIN
09577835	Not Issued	135	05/25/2000	PASSIVATION OF SIDEWALLS OF A WORD LINE STACK	LI, WEIMIN
09537445	Not Issued	168	03/27/2000	LOW K INTERLEVEL DIELECTRIC LAYER	LI, WEIMIN

				FABRICATION METHODS	
09536037	Not Issued	092	03/27/2000	LOW K INTERLEVEL DIELECTRIC LAYER FABRICATION METHODS	LI, WEIMIN
09505608	6472309	150	02/17/2000	IN SITU PLASMA PRE-DEPOSITION WAFER TREATMENT IN CHEMICAL VAPOR DEPOSITION TECHNOLOGY FOR SEMICONDUCTOR INTEGRATED CIRCUIT APPLICATIONS	LI, WEIMIN
09388826	Not Issued	061	09/01/1999	LOW K INTERLEVEL DIELECTRIC LAYER FABRICATION METHODS	LI, WEIMIN
09388570	6395647	150	09/02/1999	CHEMICAL TREATMENT OF SEMICONDUCTOR SUBSTRATES	LI, WEIMIN
09376232	6198144	150	08/18/1999	PASSIVATION OF SIDEWALLS OF A WORD LINE STACK	LI, WEIMIN
09354572	6368988	150	07/16/1999	COMBINED GATE CAP OR DIGIT LINE AND SPACER DEPOSITION USING HDP	LI, WEIMIN
09200035	6156674	150	11/25/1998	SEMICONDUCTOR PROCESSING METHODS OF FORMING INSULATIVE MATERIALS	LI, WEIMIN
09146843	6323101	150	09/03/1998	SEMICONDUCTOR PROCESSING METHODS, METHODS OF FORMING SILICON DIOXIDE, METHODS OF FORMING TRENCH ISOLATION REGIONS, AND METHODS OF FORMING INTERLEVEL DIELECTRIC LAYERS	LI, WEIMIN
09076253	6218288	150	05/11/1998	MULTIPLE STEP METHODS FOR FORMING CONFORMAL LAYERS	LI, WEIMIN
09056309	6372643	150	04/07/1998	METHOD FOR FORMING A SELECTIVE CONTACT AND LOCAL INTERCONNECT IN SITU AND SEMICONDUCTOR DEVICES CARRYING THE SAME	LI, WEIMIN
09023523	6136690	150	02/13/1998	IN SITU PLASMA PRE-	LI, WEIMIN

				DEPOSITION WAFER TREATMENT IN CHEMICAL VAPOR DEPOSITION TECHNOLOGY FOR SEMICONDUCTOR INTEGRATED CIRCUIT APPLICATIONS	

Inventor Search Completed: No Records to Display.

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Inventor Name Search Result

Your Search was:

Last Name = SANDHU
First Name = GURTEJ

Application#	Patent#	Status	Date Filed	Title	Inventor Name 49
11027825	Not Issued	020	12/29/2004	APPARATUS FOR FORMING THIN LAYERS OF MATERIALS ON MICRO-DEVICE WORKPIECES	SANDHU, GURTEJ
10973343	Not Issued	020	10/27/2004	STRUCTURALLY-STABILIZED CAPACITORS AND METHOD OF MAKING OF SAME	SANDHU, GURTEJ
10669384	Not Issued	030	09/24/2003	METHODS FOR FORMING CONDUCTIVE STRUCTURES AND STRUCTURES REGARDING SAME	SANDHU, GURTEJ
10665151	Not Issued	041	09/22/2003	STRUCTURALLY-STABILIZED CAPACITORS AND METHOD OF MAKING OF SAME	SANDHU, GURTEJ
10615524	Not Issued	092	07/03/2003	HAZE-FREE BST FILMS	SANDHU, GURTEJ
10614489	6852593	150	07/03/2003	HAZE-FREE BST FILMS	SANDHU, GURTEJ
10614418	Not Issued	094	07/03/2003	HAZE-FREE BST FILMS	SANDHU, GURTEJ
10409145	6765250	150	04/09/2003	SELF-ALIGNED, TRENCHLESS MANGETORESITIVE RANDOM-ACCESS MEMORY (MRAM) STRUCTURE WITH SIDEWALL CONTAINMENT OF MRAM STRUCTURE	SANDHU, GURTEJ
10408450	6689624	150	04/08/2003	METHOD OF FORMING SELF-ALIGNED, TRENCHLESS MAGNETORESITIVE RANDOM-ACCESS MEMORY (MRAM) STRUCTURE WITH SIDEWALL CONTAINMENT OF MRAM STRUCTURE	SANDHU, GURTEJ

10389910	6835980	150	03/18/2003	SEMICONDUCTOR DEVICE WITH NOVEL FILM COMPOSITION	SANDHU, GURTEJ
10175861	Not Issued	071	06/21/2002	METHOD OF FORMING A NON-VOLATILE ELECTRON STORAGE MEMORY AND THE RESULTING DEVICE	SANDHU, GURTEJ
10093394	Not Issued	061	03/11/2002	VERSATILE ATOMIC LAYER DEPOSITION APPARATUS	SANDHU, GURTEJ
10059308	6596636	150	01/31/2002	ALD METHOD TO IMPROVE SURFACE COVERAGE	SANDHU, GURTEJ
10039215	Not Issued	071	01/03/2002	TOP ELECTRODE IN A STRONGLY OXIDIZING ENVIRONMENT	SANDHU, GURTEJ
09982954	Not Issued	120	10/22/2001	ATOMIC LAYER DOPING APPARATUS AND METHOD	SANDHU, GURTEJ
09971945	6660535	150	10/04/2001	METHOD OF FORMING HAZE-FREE BST FILMS	SANDHU, GURTEJ
09785447	6462313	150	02/20/2001	METHOD AND APPARATUS TO CONTROL TEMPERATURE IN AN RTP SYSTEM	SANDHU, GURTEJ
09779219	6395602	150	02/07/2001	METHOD OF FORMING A CAPACITOR	SANDHU, GURTEJ
09716288	6355561	150	11/21/2000	ALD METHOD TO IMPROVE SURFACE COVERAGE	SANDHU, GURTEJ
09711206	6534357	150	11/09/2000	METHODS FOR FORMING CONDUCTIVE STRUCTURES AND STRUCTURES REGARDING SAME	SANDHU, GURTEJ
09653553	6541353	150	08/31/2000	ATOMIC LAYER DOPING APPARATUS AND METHOD	SANDHU, GURTEJ
09652863	6682969	150	08/31/2000	TOP ELECTRODE IN A STRONGLY OXIDIZING ENVIRONMENT	SANDHU, GURTEJ
09627649	Not Issued	092	07/28/2000	INTERLEVEL DIELECTRIC STRUCTURE	SANDHU, GURTEJ
09627381	6841463	150	07/28/2000	INTERLEVEL DIELECTRIC STRUCTURE AND METHOD OF FORMING SAME	SANDHU, GURTEJ
09570340	Not Issued	041	05/12/2000	ATOMIC LAYER DEPOSITION APPARATUS	SANDHU, GURTEJ
09495719	6667502	150	02/01/2000	STRUCTURALLY-STABILIZED CAPACITORS AND METHOD OF MAKING OF SAME	SANDHU, GURTEJ

09447981	6686288	150	11/23/1999	INTEGRATED CIRCUIT HAVING SELF-ALIGNED CVD-TUNGSTEN/TITANIUM CONTACT PLUGS STRAPPED WITH METAL INTERCONNECT AND METHOD OF MANUFACTURE	SANDHU, GURTEJ
09439944	Not Issued	161	11/12/1999	METHOD FOR IN-SITU CLEANING OF INDUCTIVELY-COUPLED PLASMA CHAMBERS	SANDHU, GURTEJ
09387775	6331379	150	09/01/1999	IMPROVED PHOTOLITHOGRAPHY PROCESS USING MULTIPLE ANTI-REFLECTIVE COATINGS	SANDHU, GURTEJ
09386316	Not Issued	168	08/31/1999	STRUCTURALLY-STABILIZED CAPACITORS AND METHOD OF MAKING OF SAME	SANDHU, GURTEJ
09382753	6319764	150	08/25/1999	METHOD OF FORMING HAZE-FREE BST FILMS	SANDHU, GURTEJ
09377273	6171943	150	08/19/1999	METHODS OF FORMING A CONTACT HAVING TITANIUM SILICIDE FORMED BY CHEMICAL VAPOR DEPOSITION	SANDHU, GURTEJ
09354572	6368988	150	07/16/1999	COMBINED GATE CAP OR DIGIT LINE AND SPACER DEPOSITION USING HDP	SANDHU, GURTEJ
09334753	6423626	150	06/16/1999	REMOVAL OF METAL CUSP FOR IMPROVED CONTACT FILL	SANDHU, GURTEJ
09267990	6380754	150	03/12/1999	REMOVABLE ELECTRICAL INTERCONNECT APPARATUS INCLUDING AN ENGAGEMENT PROBE	SANDHU, GURTEJ
09251387	6214687	150	02/17/1999	METHOD OF FORMING A CAPACITOR AND A CAPACITOR CONSTRUCTION	SANDHU, GURTEJ
09249659	6107686	150	02/12/1999	INTERLEVEL DIELECTRIC STRUCTURE	SANDHU, GURTEJ
09184489	5963832	150	11/02/1998	REMOVAL OF METAL CUSP FOR IMPROVED CONTACT FILL	SANDHU, GURTEJ
09146839	6727190	150	09/03/1998	METHODS OF FORMING INSULATING MATERIALS	SANDHU, GURTEJ

09041984	6455394	150	03/13/1998	METHOD FOR TRENCH ISOLATION BY SELECTIVE DEPOSITION OF LOW TEMPERATURE OXIDE FILMS	SANDHU, GURTEJ
08821936	5762537	150	03/21/1997	SYSTEM FOR REAL-TIME CONTROL OF SEMICONDUCTOR WAFER POLISHING INCLUDING HEATER	SANDHU, GURTEJ
08738789	5955758	150	10/29/1996	METHOD OF FORMING A CAPACITOR PLATE AND A CAPACITOR INCORPORATING SAME	SANDHU, GURTEJ
08631445	5789317	150	04/12/1996	LOW TEMPERATURE REFLOW METHOD FOR FILLING HIGH ASPECT RATIO CONTACTS	SANDHU, GURTEJ
08621157	Not Issued	161	03/21/1996	METHOD AND APPARATUS FOR TESTING SEMICONDUCTOR CIRCUITRY FOR OPERABILITY AND METHOD OF FORMING APPARATUS FOR TESTING SEMICONDUCTOR CIRCUITRY FOR OPERABILITY	SANDHU, GURTEJ
08594842	5730835	150	01/31/1996	FACET ETCH FOR IMPROVED STEP COVERAGE OF INTEGRATED CIRCUIT CONTACTS	SANDHU, GURTEJ
08582385	6218237	150	01/03/1996	METHOD OF FORMING A CAPACITOR	SANDHU, GURTEJ
08572846	5959327	150	12/14/1995	CAPACITOR COMPATIBLE WITH HIGH DIELECTRIC CONSTANT MATERIALS HAVING A LOW CONTACT RESISTANCE LAYER AND THE METHOD FOR FORMING SAME	SANDHU, GURTEJ
08512234	6040020	150	08/07/1995	METHOD OF FORMING A FILM HAVING ENHANCED REFLOW CHARACTERISTICS AT LOW THERMAL BUDGET	SANDHU, GURTEJ

Search and Display More Records.

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117/89, 93, 95, 102

10/669,667 **Examiner's Notes**

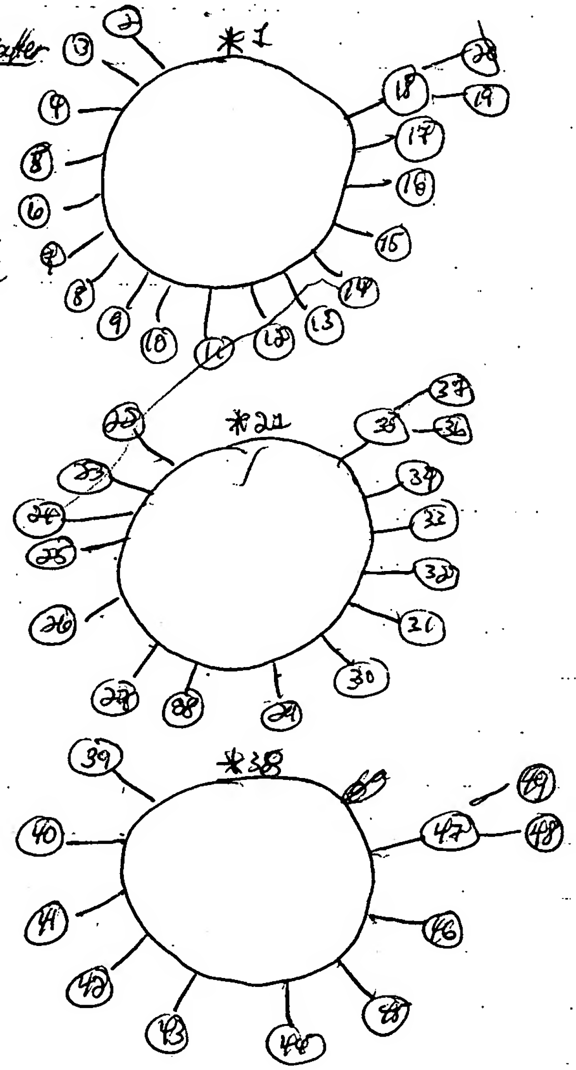
S(ALD or atomic(w)layer(w)deposit?)
S(alter? or vary? or differ? or control? or adjust?)(8a)(flow? or flow?(6a)rate? or flow?(6a)
S(SiO2 or silicon(w)dioxide)
S(substrate)(6a)(position? or placement)
S(~~flow?)(8a)~~ (trimethylsilane)
S(chemisorb)
S(flow?)(8a)(oxidant?)
S(repeat?)(8a)(inert(w)gas?)
S(first) ~~and second?~~
S(second)(6a)(inert(w)gas)

Drawings (Object)

- In Fig 2, Item #30 not mentioned in specification

Allowable Subject Matter
~~Claims 21-48~~

112#2 Rej
claims 1, 27 & 28, line 4, respectively, "trimethylsilane" does not have proper antecedence



Search History

STN
(HCAPLUS, INSPEC, JAPIO, USPATFULL, IN PADX)
5/23/05

=> d l11 1-5 abs,bib

L11 ANSWER 1 OF 5 USPATFULL on STN
AB A substrate is positioned within a deposition chamber. **Trimethylsilane** is flowed to the chamber and a first inert gas is flowed to the chamber under conditions effective to chemisorb a first species monolayer comprising silicon onto the substrate. The first inert gas is flowed at a first rate. After forming the first species monolayer, an oxidant is flowed to the chamber and a second inert gas is flowed to the chamber under conditions effective to react the oxidant with the chemisorbed first species and form a monolayer comprising **silicon dioxide** on the substrate. The second inert gas flowing is at a second rate which is less than the first rate. The a) **trimethylsilane** and first inert gas flowing and the b) oxidant and second inert gas flowing are successively repeated effective to form a **silicon dioxide** comprising layer on the substrate. Other implementations and aspects are contemplated.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.
AN 2005:71949 USPATFULL
TI **Atomic layer deposition** methods of forming **silicon dioxide** comprising layers
IN Li, Li, Meridian, ID, UNITED STATES
Li, Weimin, Boise, ID, UNITED STATES
Sandhu, Gurtej S., Boise, ID, UNITED STATES
PI US 2005061234 A1 20050324
AI US 2003-669667 A1 20030923 (10)
DT Utility
FS APPLICATION
LREP WELLS ST. JOHN P.S., 601 W. FIRST AVENUE, SUITE 1300, SPOKANE, WA, 99201
CLMN Number of Claims: 49
ECL Exemplary Claim: 1
DRWN 1 Drawing Page(s)
LN.CNT 526
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L11 ANSWER 2 OF 5 USPATFULL on STN
AB One embodiment of the present invention is a cluster tool for processing wafers that includes: (a) one or more chemical vapor deposition chambers; (b) one or more e-beam treatment chambers; and (c) a transfer chamber adapted to transfer a wafer from one chamber to another while maintaining vacuum conditions.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.
AN 2004:91974 USPATFULL
TI Cluster tool for E-beam treated films
IN Moghadam, Farhad, Saratoga, CA, UNITED STATES
Zhao, Jun, Cupertino, CA, UNITED STATES
Weidman, Timothy, Sunnyvale, CA, UNITED STATES
Roberts, Rick J., Sunnyvale, CA, UNITED STATES
Xia, Li-Qun, Santa Clara, CA, UNITED STATES
Demos, Alexandros T., Fremont, CA, UNITED STATES
PI US 2004069410 A1 20040415
AI US 2003-655276 A1 20030903 (10)
RLI Continuation of Ser. No. US 2003-428374, filed on 1 May 2003, PENDING
PRAI US 2002-378799P 20020508 (60)
DT Utility
FS APPLICATION
LREP PATENT COUNSEL, MS/2061, APPLIED MATERIALS, INC., Legal Affairs Department, P.O. Box 450A, Santa Clara, CA, 95052
CLMN Number of Claims: 14
ECL Exemplary Claim: 1
DRWN 8 Drawing Page(s)
LN.CNT 2658
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L11 ANSWER 3 OF 5 USPATFULL on STN

AB A method of forming (and apparatus for forming) refractory metal nitride layers (including silicon nitride layers), such as a tantalum nitride barrier layer, on a substrate by using an **atomic layer deposition** process (a vapor deposition process that includes a plurality of deposition cycles) with a refractory metal precursor compound, an organic amine, and an optional silicon precursor compound.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.
AN 2004:57596 USPATFULL
TI Systems and methods for forming refractory metal nitride layers using organic amines
IN Vaartstra, Brian A., Nampa, ID, UNITED STATES
PA MICRON TECHNOLOGY, INC., Boise, ID (U.S. corporation)
PI US 2004043600 A1 20040304
AI US 2002-229743 A1 20020828 (10)
DT Utility
FS APPLICATION
LREP MUETING, RAASCH & GEBHARDT, P.A., P.O. BOX 581415, MINNEAPOLIS, MN, 55458
CLMN Number of Claims: 55
ECL Exemplary Claim: 1
DRWN 2 Drawing Page(s)
LN.CNT 1076
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L11 ANSWER 4 OF 5 USPATFULL on STN
AB One embodiment of the present invention is a method for fabricating a low-k dielectric film that includes steps of: (a) chemical vapor depositing a lower-k dielectric film; and (b) e-beam treating the lower-k dielectric film.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.
AN 2003:330284 USPATFULL
TI Methods and apparatus for E-beam treatment used to fabricate integrated circuit devices
IN Moghadam, Farhad, Saratoga, CA, UNITED STATES
Zhao, Jun, Cupertino, CA, UNITED STATES
Weidman, Timothy, Sunnyvale, CA, UNITED STATES
Roberts, Rick J., Sunnyvale, CA, UNITED STATES
Xia, Li-Qun, Santa Clara, CA, UNITED STATES
Demos, Alexandros T., Fremont, CA, UNITED STATES
PI US 2003232495 A1 20031218
AI US 2003-428374 A1 20030501 (10)
PRAI US 2002-378799P 20020508 (60)
DT Utility
FS APPLICATION
LREP PATENT COUNSEL, MS/2061, APPLIED MATERIALS, INC., Legal Affairs Department, P.O.Box 450A, Santa Clara, CA, 95052
CLMN Number of Claims: 22
ECL Exemplary Claim: 1
DRWN 8 Drawing Page(s)
LN.CNT 2666
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L11 ANSWER 5 OF 5 USPATFULL on STN
AB A method for forming a metal interconnect on a substrate is provided. In one aspect, the method comprises depositing a refractory metal containing barrier layer having a thickness that exhibits a crystalline like structure and is sufficient to inhibit atomic migration on at least a portion of a metal layer by alternately introducing one or more pulses of a metal-containing compound and one or more pulses of a nitrogen-containing compound; depositing a seed layer on at least a portion of the barrier layer; and depositing a second metal layer on at least a portion of the seed layer.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.
AN 2003:180434 USPATFULL
TI Integration of **ALD** tantalum nitride and alpha-phase tantalum

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        for copper metallization application
IN      Chen, Ling, Sunnyvale, CA, UNITED STATES
        Chung, Hua, San Jose, CA, UNITED STATES
        Seutter, Sean M., San Jose, CA, UNITED STATES
        Yang, Michael X., Palo Alto, CA, UNITED STATES
        Xi, Ming, Palo Alto, CA, UNITED STATES
        Ku, Vincent, San Jose, CA, UNITED STATES
        Wu, Dien-Yeh, San Jose, CA, UNITED STATES
        Ouye, Alan, San Mateo, CA, UNITED STATES
        Nakashima, Norman, Sunnyvale, CA, UNITED STATES
        Chin, Barry, Saratoga, CA, UNITED STATES
        Zhang, Hong, Fremont, CA, UNITED STATES
PI      US 2003124262       A1   20030703
AI      US 2002-281386      A1   20021025 (10)
PRAI    US 2001-346086P      20011026 (60)
DT      Utility
FS      APPLICATION
LREP    APPLIED MATERIALS, INC., PATENT COUNSEL, Legal Affairs Department, P.O.
        BOX 450A, Santa Clara, CA, 95052
CLMN    Number of Claims: 19
ECL     Exemplary Claim: 1
DRWN    6 Drawing Page(s)
LN.CNT 1034
CAS INDEXING IS AVAILABLE FOR THIS PATENT


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     (FILE 'HOME' ENTERED AT 10:01:24 ON 23 MAY 2005)

     FILE 'HCAPLUS, INSPEC, JAPIO, USPATFULL, USPAT2, INPADOC' ENTERED AT
     10:02:21 ON 23 MAY 2005
L1         20410 S (ALD OR ATOMIC(W)LAYER(W)DEPOSIT? OR ALE OR ATOMIC(W)LAYER(W)
L2        869964 S (ALTER? OR VARY? OR CONTROL? OR DIFFER? OR ADJUST?)(8A)(FLOW?
L3        564469 S (SIO2 OR SILICON(W)DIOXIDE)
L4          6919 S (TRIMETHYLSILANE)
L5         29782 S (CHEMISORB?)
L6          4319 S (FLOW?)(6A)(OXIDANT#)
L7          2936 S (FIRST)(4A)(INERT(W)GAS?)
L8          2929 S (SECOND?)(4A)(INERT(W)GAS?)
L9             1 S L1 AND L2 AND L3 AND L4 AND L6 AND L7 AND L8
L10            1 S L1 AND L2 AND L3 AND L4 AND L6
L11            5 S L1 AND L2 AND L3 AND L4

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=> d his

     (FILE 'HOME' ENTERED AT 10:01:24 ON 23 MAY 2005)

     FILE 'HCAPLUS, INSPEC, JAPIO, USPATFULL, USPAT2, INPADOC' ENTERED AT
     10:02:21 ON 23 MAY 2005
L1         20410 S (ALD OR ATOMIC(W)LAYER(W)DEPOSIT? OR ALE OR ATOMIC(W)LAYER(W)
L2        869964 S (ALTER? OR VARY? OR CONTROL? OR DIFFER? OR ADJUST?)(8A)(FLOW?
L3        564469 S (SIO2 OR SILICON(W)DIOXIDE)
L4          6919 S (TRIMETHYLSILANE)
L5         29782 S (CHEMISORB?)
L6          4319 S (FLOW?)(6A)(OXIDANT#)
L7          2936 S (FIRST)(4A)(INERT(W)GAS?)
L8          2929 S (SECOND?)(4A)(INERT(W)GAS?)

=> s l1 and l2 and l3 and l4 and l6 and l7 and l8
L9             1 L1 AND L2 AND L3 AND L4 AND L6 AND L7 AND L8

=> d l9 abs,bib

L9   ANSWER 1 OF 1  USPATFULL on STN
AB     A substrate is positioned within a deposition chamber.
       Trimethylsilane is flowed to the chamber and a first
       inert gas is flowed to the chamber under conditions
       effective to chemisorb a first species monolayer comprising silicon onto
       the substrate. The first inert gas is
       flowed at a first rate. After forming the first species
       monolayer, an oxidant is flowed to the chamber and a
       second inert gas is flowed to the chamber
       under conditions effective to react the oxidant with the chemisorbed
       first species and form a monolayer comprising silicon
       dioxide on the substrate. The second inert
       gas flowing is at a second rate which is less than the
       first rate. The a) trimethylsilane and first
       inert gas flowing and the b) oxidant
       and second inert gas flowing are
       successively repeated effective to form a silicon
       dioxide comprising layer on the substrate. Other implementations
       and aspects are contemplated.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.
AN     2005:71949  USPATFULL
TI     Atomic layer deposition methods of forming
       silicon dioxide comprising layers
IN     Li, Li, Meridian, ID, UNITED STATES
       Li, Weimin, Boise, ID, UNITED STATES
       Sandhu, Gurtej S., Boise, ID, UNITED STATES
PI     US 2005061234      A1   20050324
AI     US 2003-669667     A1   20030923 (10)
DT     Utility
FS     APPLICATION
LREP   WELLS ST. JOHN P.S., 601 W. FIRST AVENUE, SUITE 1300, SPOKANE, WA, 99201
CLMN   Number of Claims: 49
ECL    Exemplary Claim: 1
DRWN   1 Drawing Page(s)
LN.CNT 526
CAS INDEXING IS AVAILABLE FOR THIS PATENT.
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=> d l6 1-5 abs,bib

L6 ANSWER 1 OF 5 USPATFULL on STN
AB A substrate is positioned within a deposition chamber. **Trimethylsilane** is flowed to the chamber and a first inert gas is flowed to the chamber under conditions effective to chemisorb a first species monolayer comprising silicon onto the substrate. The first inert gas is flowed at a first rate. After forming the first species monolayer, an oxidant is flowed to the chamber and a second inert gas is flowed to the chamber under conditions effective to react the oxidant with the chemisorbed first species and form a monolayer comprising **silicon dioxide** on the substrate. The second inert gas flowing is at a second rate which is less than the first rate. The a) **trimethylsilane** and first inert gas flowing and the b) oxidant and second inert gas flowing are successively repeated effective to form a **silicon dioxide** comprising layer on the substrate. Other implementations and aspects are contemplated.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.
AN 2005:71949 USPATFULL
TI **Atomic layer deposition** methods of forming **silicon dioxide** comprising layers
IN Li, Li, Meridian, ID, UNITED STATES
Li, Weimin, Boise, ID, UNITED STATES
Sandhu, Gurtej S., Boise, ID, UNITED STATES
PI US 2005061234 A1 20050324
AI US 2003-669667 A1 20030923 (10)
DT Utility
FS APPLICATION
LREP WELLS ST. JOHN P.S., 601 W. FIRST AVENUE, SUITE 1300, SPOKANE, WA, 99201
CLMN Number of Claims: 49
ECL Exemplary Claim: 1
DRWN 1 Drawing Page(s)
LN.CNT 526
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L6 ANSWER 2 OF 5 USPATFULL on STN
AB One embodiment of the present invention is a cluster tool for processing wafers that includes: (a) one or more chemical vapor deposition chambers; (b) one or more e-beam treatment chambers; and (c) a transfer chamber adapted to transfer a wafer from one chamber to another while maintaining vacuum conditions.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.
AN 2004:91974 USPATFULL
TI Cluster tool for E-beam treated films
IN Moghadam, Farhad, Saratoga, CA, UNITED STATES
Zhao, Jun, Cupertino, CA, UNITED STATES
Weidman, Timothy, Sunnyvale, CA, UNITED STATES
Roberts, Rick J., Sunnyvale, CA, UNITED STATES
Xia, Li-Qun, Santa Clara, CA, UNITED STATES
Demos, Alexandros T., Fremont, CA, UNITED STATES
PI US 2004069410 A1 20040415
AI US 2003-655276 A1 20030903 (10)
RLI Continuation of Ser. No. US 2003-428374, filed on 1 May 2003, PENDING
PRAI US 2002-378799P 20020508 (60)
DT Utility
FS APPLICATION
LREP PATENT COUNSEL, MS/2061, APPLIED MATERIALS, INC., Legal Affairs Department, P.O. Box 450A, Santa Clara, CA, 95052
CLMN Number of Claims: 14
ECL Exemplary Claim: 1
DRWN 8 Drawing Page(s)
LN.CNT 2658
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L6 ANSWER 3 OF 5 USPATFULL on STN
AB A method of forming (and apparatus for forming) refractory metal nitride

layers (including silicon nitride layers), such as a tantalum nitride barrier layer, on a substrate by using an **atomic layer deposition** process (a vapor deposition process that includes a plurality of deposition cycles) with a refractory metal precursor compound, an organic amine, and an optional silicon precursor compound.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.
AN 2004:57596 USPATFULL
TI Systems and methods for forming refractory metal nitride layers using organic amines
IN Vaartstra, Brian A., Nampa, ID, UNITED STATES
PA MICRON TECHNOLOGY, INC., Boise, ID (U.S. corporation)
PI US 2004043600 A1 20040304
AI US 2002-229743 A1 20020828 (10)
DT Utility
FS APPLICATION
LREP MUETING, RAASCH & GEBHARDT, P.A., P.O. BOX 581415, MINNEAPOLIS, MN, 55458
CLMN Number of Claims: 55
ECL Exemplary Claim: 1
DRWN 2 Drawing Page(s)
LN.CNT 1076
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L6 ANSWER 4 OF 5 USPATFULL on STN
AB One embodiment of the present invention is a method for fabricating a low-k dielectric film that includes steps of: (a) chemical vapor depositing a lower-k dielectric film; and (b) e-beam treating the lower-k dielectric film.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.
AN 2003:330284 USPATFULL
TI Methods and apparatus for E-beam treatment used to fabricate integrated circuit devices
IN Moghadam, Farhad, Saratoga, CA, UNITED STATES
Zhao, Jun, Cupertino, CA, UNITED STATES
Weidman, Timothy, Sunnyvale, CA, UNITED STATES
Roberts, Rick J., Sunnyvale, CA, UNITED STATES
Xia, Li-Qun, Santa Clara, CA, UNITED STATES
Demos, Alexandros T., Fremont, CA, UNITED STATES
PI US 2003232495 A1 20031218
AI US 2003-428374 A1 20030501 (10)
PRAI US 2002-378799P 20020508 (60)
DT Utility
FS APPLICATION
LREP PATENT COUNSEL, MS/2061, APPLIED MATERIALS, INC., Legal Affairs Department, P.O.Box 450A, Santa Clara, CA, 95052
CLMN Number of Claims: 22
ECL Exemplary Claim: 1
DRWN 8 Drawing Page(s)
LN.CNT 2666
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L6 ANSWER 5 OF 5 USPATFULL on STN
AB A method for forming a metal interconnect on a substrate is provided. In one aspect, the method comprises depositing a refractory metal containing barrier layer having a thickness that exhibits a crystalline like structure and is sufficient to inhibit atomic migration on at least a portion of a metal layer by alternately introducing one or more pulses of a metal-containing compound and one or more pulses of a nitrogen-containing compound; depositing a seed layer on at least a portion of the barrier layer; and depositing a second metal layer on at least a portion of the seed layer.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.
AN 2003:180434 USPATFULL
TI Integration of **ALD** tantalum nitride and alpha-phase tantalum for copper metallization application

```
IN      Chen, Ling, Sunnyvale, CA, UNITED STATES
        Chung, Hua, San Jose, CA, UNITED STATES
        Seutter, Sean M., San Jose, CA, UNITED STATES
        Yang, Michael X., Palo Alto, CA, UNITED STATES
        Xi, Ming, Palo Alto, CA, UNITED STATES
        Ku, Vincent, San Jose, CA, UNITED STATES
        Wu, Dien-Yeh, San Jose, CA, UNITED STATES
        Ouye, Alan, San Mateo, CA, UNITED STATES
        Nakashima, Norman, Sunnyvale, CA, UNITED STATES
        Chin, Barry, Saratoga, CA, UNITED STATES
        Zhang, Hong, Fremont, CA, UNITED STATES
PI      US 2003124262       A1   20030703
AI      US 2002-281386      A1   20021025 (10)
PRAI    US 2001-346086P      20011026 (60)
DT      Utility
FS      APPLICATION
LREP    APPLIED MATERIALS, INC., PATENT COUNSEL, Legal Affairs Department, P.O.
        BOX 450A, Santa Clara, CA, 95052
CLMN    Number of Claims: 19
ECL     Exemplary Claim: 1
DRWN    6 Drawing Page(s)
LN.CNT 1034
CAS INDEXING IS AVAILABLE FOR THIS PATENT.


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     (FILE 'HOME' ENTERED AT 10:42:04 ON 23 MAY 2005)

     FILE 'HCAPLUS, INSPEC, JAPIO, USPATFULL, USPAT2, INPADOC' ENTERED AT
     10:42:26 ON 23 MAY 2005
L1         20410 S (ALD OR ATOMIC(W)LAYER(W)DEPOSIT? OR ALE OR ATOMIC(W)LAYER(W)
L2        564469 S (SIO2 OR SILICON(W)DIOXIDE)
L3          6919 S (TRIMETHYLSILANE)
L4            24 S L1 AND L2 AND L3
L5        875677 S (ALTER? OR VARY? OR DIFFER? OR ADJUST? OR CONTROL?)(8A)(FLOW?
L6             5 S L4 AND L5

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